## NSN 5961-01-194-1303

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View Online at https://aerobasegroup.com/nsn/5961-01-194-1303 **Inclosure Material:** Metal **Overall Length:** 1.330 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-61 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.455 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 450.0 breakdown voltage, collector-to-base, emitter open and 400.0 breakdown voltage, collector-to-emitter, base open and 7.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 20.00 amperes source cutoff current and 10.00 amperes source cutoff current **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector preset **Transfer Ratio:** 40.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab, solder lug Shelf Life: N/a

No

**Unit Of Measure:** 

Demilitarization:

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